

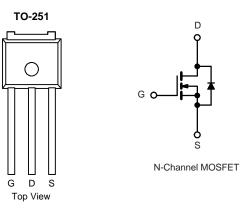
VS5812AI-VB Datasheet N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a		
60	0.012at V _{GS} = 10 V	55		
60	0.015 at V _{GS} = 4.5 V	47		

FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET
- Material categorization:





ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current /T 175 °C)b	T _C = 25 °C	1-	55		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 100 °C	I I _D	46 ^a		
Pulsed Drain Current	I _{DM}	110	A		
Continuous Source Current (Diode Conduction)	۱ _S	50 ^a			
Avalanche Current	I _{AS}	50			
Single Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Maximum Dawar Dissinction	T _C = 25 °C	P	136	W	
Maximum Power Dissipation	T _A = 25 °C	• P _D —	3 ^b , 8.3 ^{b, c}		
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Mauiauna lunation ta Arabianta	$t \le 10 \text{ sec}$	R _{thJA}	15	18	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		40	50		
Maximum Junction-to-Case		R _{thJC}	0.85	1.1		

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t \leq 10 s.



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static	• • • • • • •			Typ.		•	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 µA	_{IS} = 0 V, I _D = 250 μA 60				
Gate Threshold Voltage	V _{GS(th)}				3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μA	
-		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	60			Α	
		V _{GS} = 10 V, I _D = 20 A		0.012		- Ω	
	Р	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.013			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.017			
		V _{GS} = 4.5 V, I _D = 15 A		0.015		1	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic							
Input Capacitance	C _{iss}			3650			
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		570		pF	
Reverse Transfer Capacitance	C _{rss}			325			
Total Gate Charge ^c	Qg			46			
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 50 A		10		nC	
Gate-Drain Charge ^c	Q _{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω		15	25	20	
Turn-Off Delay Time ^c	t _{d(off)}	$\text{I}_\text{D}\cong$ 50 A, V_GEN = 10 V, R_g = 2.5 Ω		35	50	ns	
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				60	А	
Diode Forward Voltage	V_{SD}	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns	

SPECIFICATIONS (T₁ = 25 °C, unless otherwise noted)

Notes:

a. For design aid only; not subject to production testing.

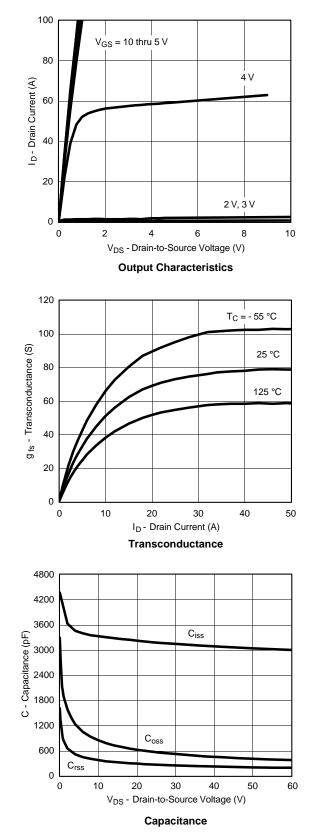
b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

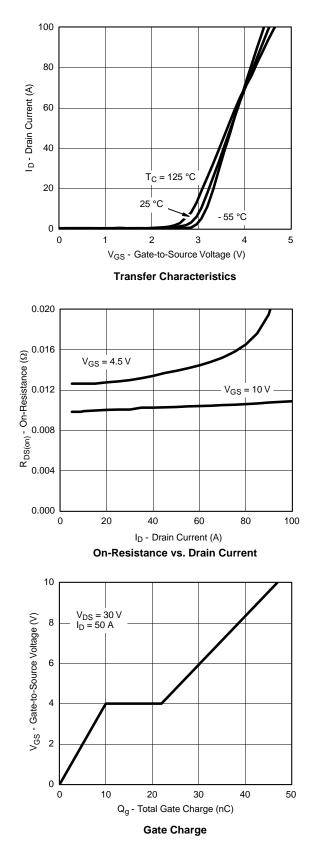
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



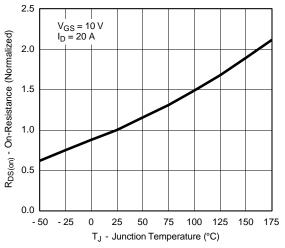
TYPICAL CHARACTERISTICS (25 °C unless noted)



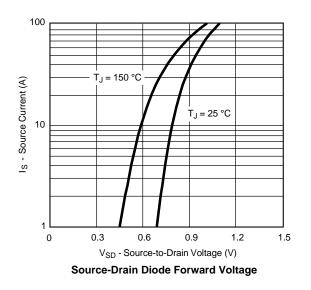




TYPICAL CHARACTERISTICS (25 °C unless noted)

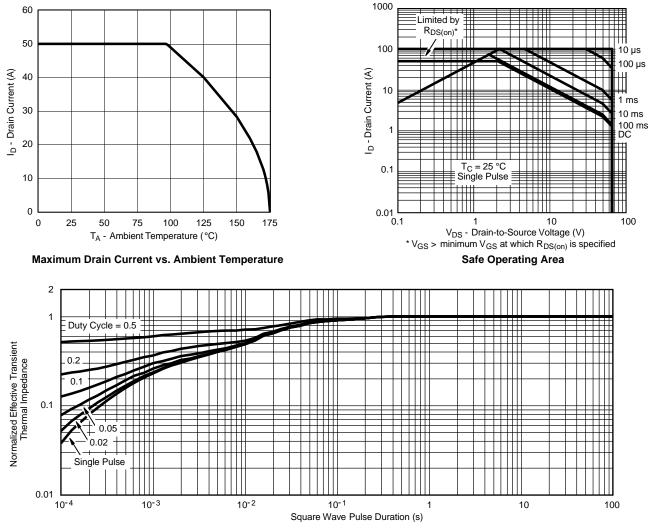


On-Resistance vs. Junction Temperature





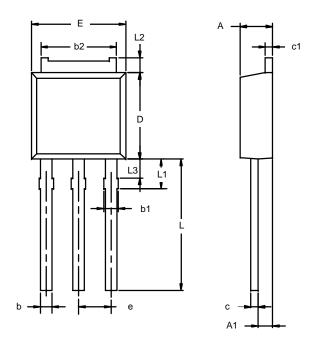
THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

	MILLIN	IETERS	INC	HES		
Dim	Min	Мах	Min	Max		
Α	2.21	2.38	0.087	0.094		
A1	0.89	1.14	0.035	0.045		
b	0.71	0.89	0.028	0.035		
b1	0.76	1.14	0.030	0.045		
b2	5.23	5.43	0.206	0.214		
С	0.46	0.58	0.018	0.023		
c1	0.46	0.58	0.018	0.023		
D	5.97	6.22	0.235	0.245		
Е	6.48	6.73	0.255	0.265		
е	2.28	BSC	0.090 BSC			
L	8.89	9.53	0.350	0.375		
L1	1.91	2.28	0.075	0.090		
L2	0.89	1.27	0.035	0.050		
L3	1.15	1.52	0.045	0.060		
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346						



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